



CSP MOSFET 数据手册

NP017B020CSPA

CSP 20V Typ 17mΩ Dual N-Channel MOSFET

Rev. 1.1

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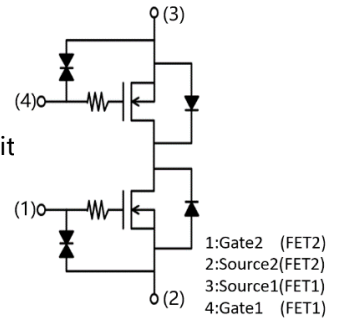
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CSP 20V Typ 17mΩ Dual N-Channel NP017B020CSPA

产品特性 Features

- ◆ 2.5V 驱动电压 2.5 V Drive
- ◆ 共漏极结构, 设计方便 Common-Drain Configuration for Design Simplicity
- ◆ 低的导通电阻 Low Source-Source ON Resistance
- ◆ 2kV HBM 栅极静电保护 2kV HBM ESD Diode-Protected Gate
- ◆ 无铅引脚, 无卤化符合 RoHS 要求 Pb-Free, Halogen Free and RoHS Compliance

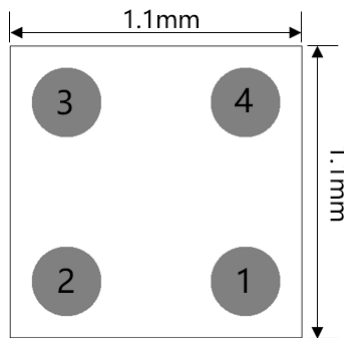


原理图
Schematic diagram

应用领域 Applications

- ◆ 单节锂电池充放电开关 1-Cell Lithium-ion Battery Charging and Discharging Switch
- ◆ 锂电池保护开关 Battery Protection Switch

关键参数与封装信息 Key Performance and Package Parameters



1:Gate2 (FET2)
2:Source2(FET2)
3:Source1(FET1)
4:Gate1 (FET1)
Package Type:CSP
Size:1.1(mm)×1.1(mm)×0.30(mm)

产品型号 Part No.	封装 Package	源极到源极电压 V_{ss} (TYP)	源极电流最大值 I_s Max	导通电阻 $R_{SS(on)}$	印记 Marking
NP017B020CSPA	CSP	20V	3A	17.0 mΩ@4.5 V	17A
				19.5 mΩ@3.8 V	
				21.0 mΩ@3.1 V	
				24.5 mΩ@2.5 V	

最大额定值 Maximum Ratings^①

参数 Parameter	符号 Symbol	数值 Value	单位 Unit
源极-源极击穿电压 Source-Source Breakdown Voltage	BV_{SSS}	19.2	V
栅极-源极电压 Gate to Source Voltage	V_{GS}	± 8	V
直流源极电流 Source Current (DC)	I_S	3	A
脉冲源电极电流 Source Current (Pulse) $PW \leq 10\mu s, Duty Cycle \leq 1\%$	I_{Sp}	18	A
耗散功率 Power Dissipation	P_D	0.4	W
结温 Operating Junction Temperature	T_J	-55...+150	$^{\circ}C$
存储温度 Storage Temperature	T_{Stg}	-55...+150	$^{\circ}C$

① 超过最大额定值表中列出的使用条件可能会损坏芯片。如果超过这些限制值中的任何一个，则芯片的功能可能无法保证，芯片可能发生损坏并影响可靠性。

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

热阻特性 Thermal Resistance^②

参数 Parameter	符号 Symbol	数值 (最大) Max. Value	单位 Unit
结到环境热阻 Thermal Resistance Junction to Ambient	$R_{\theta JA}$	312.5	$^{\circ}C/W$

② 芯片表面贴于 70mmX70mm 环氧树脂 PCB 板。

Surface mounted on Mounted on 70mmx70mm FR4 board

电气特性 Electrical Characteristics ($T_j = 25^\circ\text{C}$ unless otherwise noted)

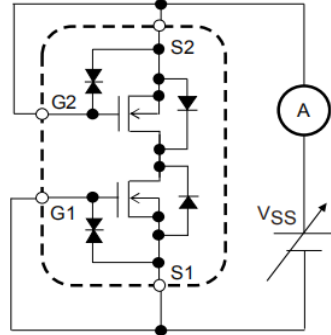
项目③ Parameter	符号 Symbol	测试条件 Conditions	数值 Value			单位 Unit
			Min.	Typ.	Max.	
源极-源极击穿电压 Source to Source Breakdown Voltage	$V_{(BR)SSS}$	$I_S = 1\text{ mA}$, $V_{GS} = 0\text{ V}$ Test Circuit 1	19.2	20.5	-	V
零栅压下源极漏电流 Zero Gate Voltage Source Current	I_{SSS}	$V_{SS} = 16\text{ V}$, $V_{GS} = 0\text{ V}$ Test Circuit 1	-	-	1.0	μA
栅极-源极漏电流 Gate to Source Leakage Current	I_{GSS1}	$V_{GS} = \pm 5\text{ V}$, $V_{SS} = 0\text{ V}$ Test Circuit 2	-	-	± 1.5	μA
栅极-源极漏电流 Gate to Source Leakage Current	I_{GSS2}	$V_{GS} = \pm 8\text{ V}$, $V_{SS} = 0\text{ V}$ Test Circuit 2	-	-	± 10	μA
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{SS} = 6\text{ V}$, $I_S = 1\text{ mA}$ Test Circuit 3	0.4	-	1.0	V
源极到源极直流导通电阻 Static Source to Source On-State Resistance	$R_{SS(on)}$	$I_S = 2\text{ A}$, $V_{GS} = 4.5\text{ V}$ Test Circuit 4	10	17.0	26	$\text{m}\Omega$
		$I_S = 2\text{ A}$, $V_{GS} = 3.8\text{ V}$ Test Circuit 4	11	19.5	26.5	$\text{m}\Omega$
		$I_S = 2\text{ A}$, $V_{GS} = 3.1\text{ V}$ Test Circuit 4	12	21.0	34	$\text{m}\Omega$
		$I_S = 2\text{ A}$, $V_{GS} = 2.5\text{ V}$ Test Circuit 4	13	24.5	48	$\text{m}\Omega$
源极到源极正向压降 Forward Source to Source Voltage	$V_{F(S-S)}$	$I_S = 1\text{ A}$, $V_{GS} = 0$ Test Circuit 7	0.4	0.66	1.0	V

③ 产品的参数性能按照上述表格参数所描述，除非有额外的说明。如果产品工作在其他不同的条件下，产品的电学性能可能并不遵守上述参数。

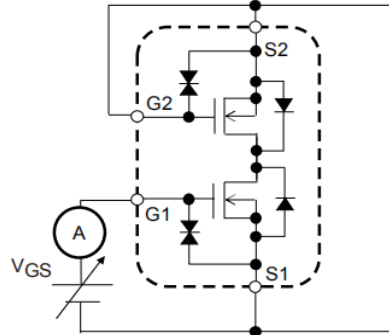
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

测试电路范例 Test Circuits Example

Test Circuit 1
V_{SS} / I_{SS}

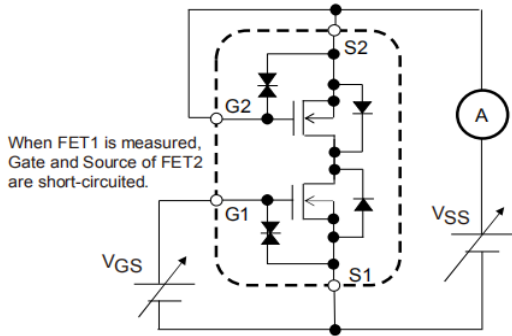


Test Circuit 2
I_{GSS}



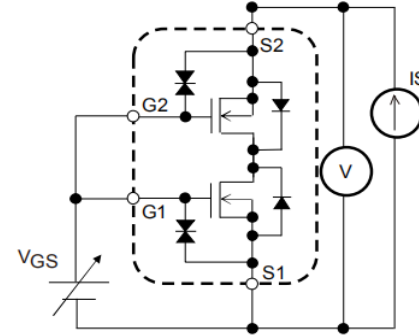
When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 3
V_{GS(th)}

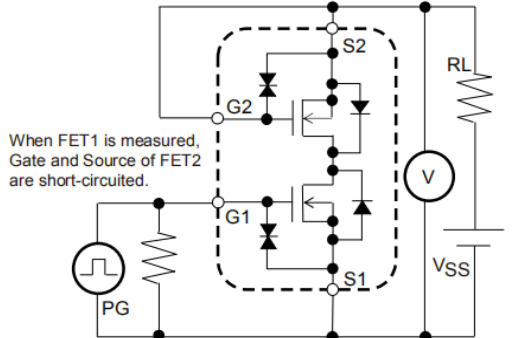


When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 4
R_{SS(on)}

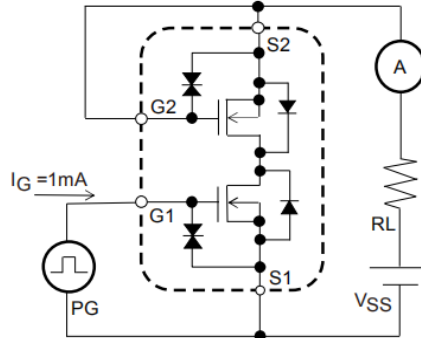


Test Circuit 5
t_{d(on)}, t_r, t_{d(off)}, t_f



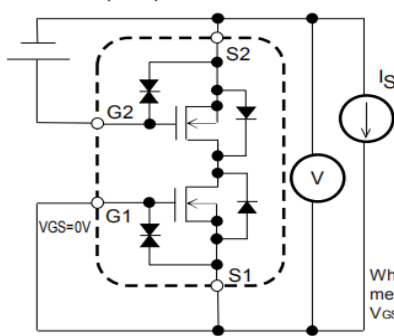
When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 6
Q_g



When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 7
V_{F(S-S)}



When FET1 is measured, +4.5V is added to V_{GS} of FET2.

特征电学和温度曲线 Typical Electrical and Thermal Characteristics

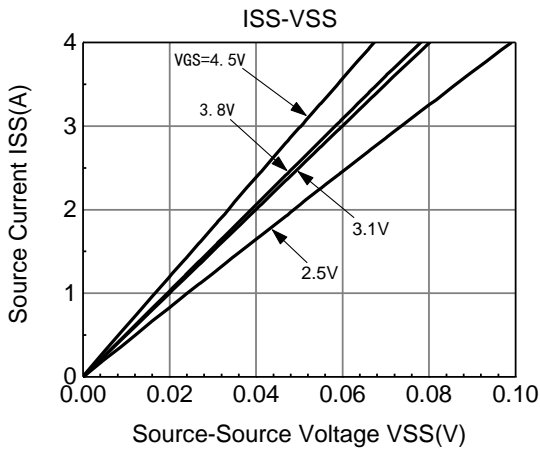


Figure 1: On-Region Characteristics

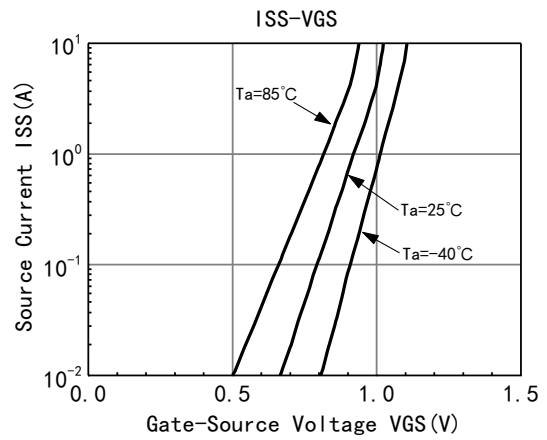


Figure 2: Typical Transfer Characteristics

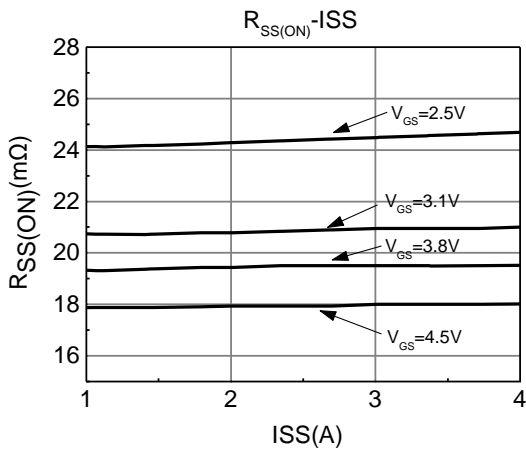


Figure 3: On-Resistance vs. Source Current and Gate Voltage

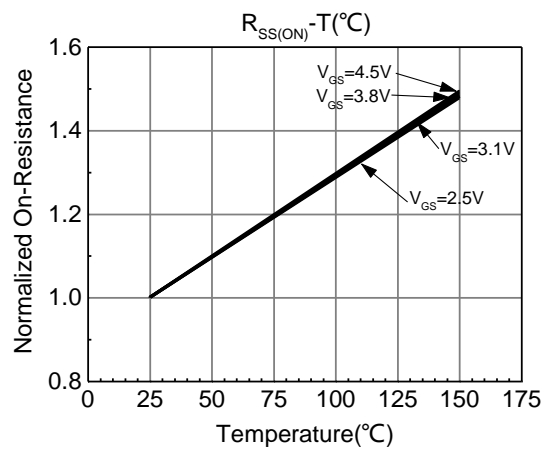


Figure 4: On-Resistance vs. Junction Temperature

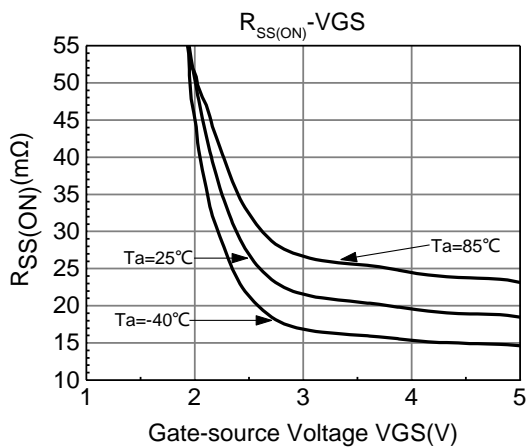


Figure 5: On-Resistance vs. Gate- Source Voltage

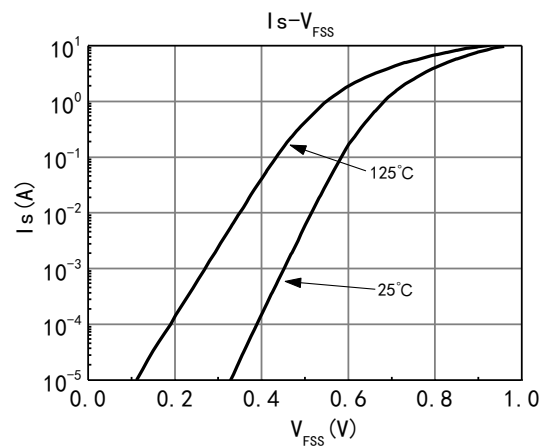


Figure 6: Forward Source to Source Characteristics

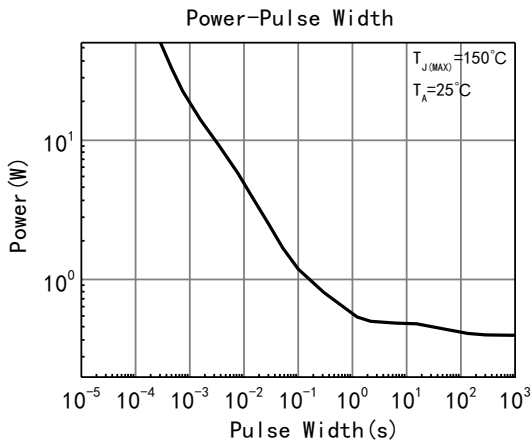


Figure 7: Single Pulse Power Rating Junction to Ambient

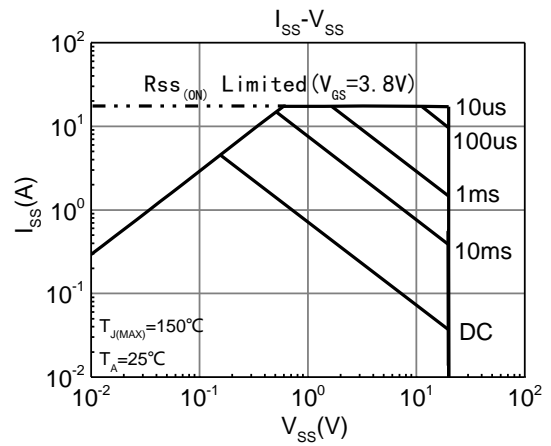


Figure 8: Safe Operating Area

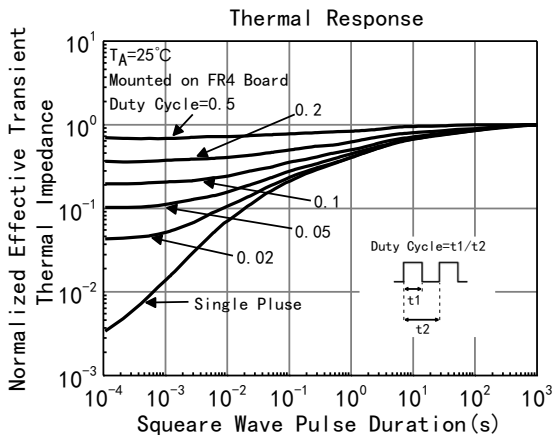
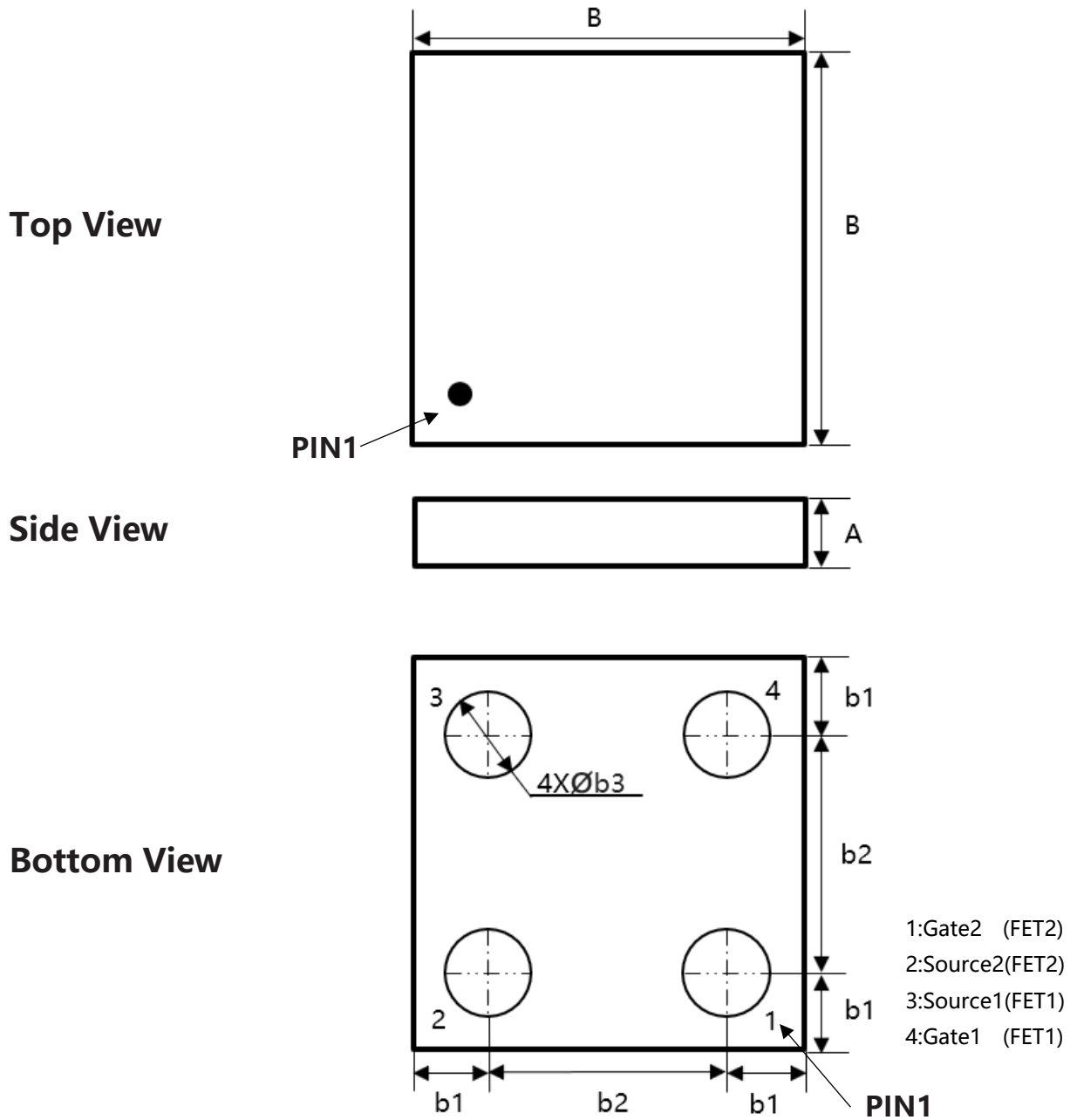


Figure 9: Normalized Maximum Transient Thermal Impedance

封装尺寸 Package Dimensions



Symbol	Dimensions In Millimeters			Dimensions In Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.27	0.3	0.33	0.0106	0.0118	0.0130
B	1.05	1.1	1.15	0.0413	0.0433	0.0453
b1	0.185	0.225	0.265	0.0073	0.0089	0.0104
b2	0.62	0.65	0.68	0.0244	0.0256	0.0268
b3	0.2	0.25	0.3	0.0079	0.0098	0.0118

历史版本 Version history

版本号	时间	修改内容
V1.0	2022 年 01 月	初始版本
V1.1	2022 年 03 月	更新 PAD 定义